

第2回 EUV-FEL WOOK 2017 12.12Tue 10:00-17:00

HIGH POWER LPP-EUV SOURCE WITH LONG COLLECTOR MIRROR LIFETIME FOR HIGH VOLUME SEMICONDUCTOR MANUFACTURING

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Agenda

Motivation

HVM Ready System Performance Progress and Target
HVM Ready Long-lifetime Collector Mirror
Summary



MOTIVATION



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Requirement for a Light Source in EUV Lithography



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EUV extension roadmap



ASML

Motivation

According to ASML roadmap*, EUV lithography will be released with 145wph throughput by 2019 for HVM.

- EUV source power is increasing, but has not yet reached sufficient power levels, required 250W is Ready? Q1
- In order to reach 145wph, it requires high Availability, and also one key element such as Collector Life are Ready? Q2

Gigaphoton has been integrating an architecture of LPP with CO₂ laser plus Pre-pulse since 2002, and has the longest development history in EUV.

Will Gigaphoton's source be in time to meet145wph HVM by 2019 ? Q3

* Reference: Christophe Smeets (ASML)@ EUVL Symposium- 2016



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HVM READY PERFORMANCE PROGRESS AND TARGETS



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How to generate EUV light



- Sn droplet 20um Dia.100kHz ejection with 300km/h
- Pre and main lasers shoot every single droplets.
- Collector transfer EUV light to the IF point.



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Gigaphoton's LPP Source Concept

1. Dual-wavelength shooting concept

High CE attained with CO_2 and pre-pulse solid-state lasers

2. EUV specific Hybrid CO₂ laser system

Short pulse/High repetition rate oscillator combined with commercial cw-amplifiers

3. Debris mitigation with Super conductive magnets (SM3)

4. Accurate shooting system

Stable droplet generation and shooting beam control

5. Out-of-band light reduction

Grating structured collector mirror





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Current EUV Sources at Gigaphoton



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Pre-pulse Technology

Higher CE and Power

- Optimum wavelength to transform droplets into fine mists
- High CE is achieved with ideal expansion of the fine mists to match the CO₂ laser beam diameter

Long Life Chamber

- Debris mitigation by superconducting magnets
- Ionized tin atoms are guided to tin catchers by the magnetic field





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Pre-Pulse Technology







Conversion Efficiency





20um diameter-droplets with 900 um interval are ejected at 100kHz.

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Pilot System Driver Laser and PPL System



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Target System Specification

		Proto#1	Proto#2 Key Technology	Pilot#1 HVM Ready	
Target Performance	EUV Power	25W	>100W	250W	
	CE	3%	> 4%	> 5%	
	Pulse Rate	100kHz	100kHz	100kHz	
	Output Angle	Horizontal	62°upper	62°upper	
	Availability	~1 week	~1 week	>80%	
echnology	Droplet Generator	20 - 25 <i>µ</i> m	< 20 <i>µ</i> m	< 20 µm	
	CO ₂ Laser	5kW	20kW	27kW	
	Pre-pulse Laser	picosecond	picosecond	picosecond	
	Collector Mirror Lifetime	Used as development platform	10 days	> 3 months	

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Key Performance Status and its target

	2015	2016	2017 Current	2018
In-band power (Average Power)	87W (83W)	113W (111W)	113W (91W)	250W
Collector lifetime*1	No data	-10%/Bpls *3	-0.4%/Bpls	-0.2%/Bpls
Availability*2	15%	44%	53%	> 80%

Proto #2

Pilot #1

- *1, Collector lifetime estimation has been started from 2017
- *2, Max availability in 4 week operation.
- *3, Main issue was capping layer performance.

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Power and Stability at Continuous Operation

Performance In-band power 120

Average power at IF	85W
Dose error (3 sigma)	0.04%
Die yield (< 0.16%)	99.4 %
Operation time	143h
Pulse Number	19Bpls
Duty cycle	75%
In-band power	113W
Dose margin	35%
CE	4.4%
Availability 4wk	32%
Collector lifetime	-10%/Bpls
Repetition rate	50kHz
CO2 power	12kW
Note	

Burst pattern: 1000ms ON, 333ms OFF Dose error: including pre-exposure phase(10ms) Die yield: defined by 0.16% dose error



Dose error was mainly due to droplet combination failure and it was improved by droplet generator improvement(but not perfect).

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EUV power: 250W achieved

Experimental data

Proto#2: 250W with 4% CE at 100KHz





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Availability potential test



<u>Dose error</u>: System stopped at > 2% dose error (3 sigma) /10kpls slit and error was not recovered by automatic function <u>Idle time</u>: Time for waiting operators.

24 hour x 7 days definition: Unmanned operation between 9pm thru 8am



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High Power EUV Source for High NA EUV Exposure Tool

											Lithography	R(nm)*	NA		
EUV ave.Power[W]			ver[W]	V] Conversion Efficiency [%]									(nm)	(•••)	
@100kHz				2%	3%	4%	5%	<mark>6%</mark>	7%	8%	KrF dry	102	0.85	248	40
CO2 laser Energy [mJ]	15		1.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	ArF dry	73	0.93	193	45
	50		5	19.1	28.7	38.2	47.8	57.3	66.9	76.4	F ₂ drv	69	0.80	157	-
	100		10	46.4	69.6	92.8	<u>).0</u>	139.2	162.4	185.6	Λ Γ :	50	1.05	104	00
	150		15	73.7	110.6	147.4	1.3	221.1	258.0	294.8	Arr immersion	50	1.35	134	90
	200		20	101.0	151	202.0	5	303.0	353.5	404.0	EUV	14	0.33	13.5	>250
	250	$\overline{}$	25	128.3	192.5	256.6	320.8	384.9	449.1	513.2	EUV (High NA)	7	0.6	13.5	>500
	300	[kv	30	155.6	233.4	311.2	389.0	466.8	544.6	622.4		·			
	350	er	35	182.9	274.4	365.8	457.3	548.7	640.2	731.6					
	400	Ň	40	210.2	315.3	420.4	525.5	630.6	735.7	840.8				6-	
	450	۵.	45	237.5	356.3	475.0	593 <u>8</u>	712.5	831.3	950.0					R. 1997 -
	500	ave	50	264.8	397.2	529.6	662.0	794.4	926.8	1059.2					
	550	л С	55	292.1	438.2	584.2	730.3	876.3	1022.4	<u>1168.4</u>		HV	M1	HVM2	HVM3
	600	ase	60	319.4	479.1	638.8	798.5	958.2	1117.9	<u>1277.6</u>					
	<mark>650</mark>	2	65	346.7	520.1	693.4	866.8	1040.1	1213.5	<mark>1386.8</mark>	EUV Power	250W		300W	500W
	700	8	70	374.0	561.0	748.0	935.0	1122.0	1309.0	1496.0					
	750	Ū	75	401.3	602.0	802.6	1003.3	1203.9	1404.6	1605.2	Pulse Rate	100	kHz	100kHz	100kHz
	800		80	428.6	642.9	857.2	1071.5	1285.8	1500.1	1714.4					
	850		85	455.9	683.9	911.8	1139.8	1367.7	1595.7	1823.6	CE	4.5	5%	5%	5%
	900		90	483.2	724.8	966.4	1208.0	1449.6	1691.2	1932.8					
	950	ļ	95	510.5	765.8	1021.0	1276.3	1531.5	1786.8	2042.0	CO ₂ Laser Powe	r 25	<w< td=""><td>25kW</td><td>40kW</td></w<>	25kW	40kW
	1000		100	537.8	806.7	1075.6	1344.5	1613.4	1882.3	2151.2		251(11			

Our LPP system has capability to give 300~500W output power.



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HVM READY LONG-LIFETIME COLLECTOR MIRROR



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Pilot System EUV Chamber





HVM Collector Mirror Specifications



Size Φ412mm
Weight 22kg
Collector efficiency >74%
Collector reflectivity >48%
Grating structure



Measured IR reflectivity: 0.37%



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"SM3": Superconducting Magnet Mitigation Method

Higher CE and Power

- Optimum wavelength to transform droplets into fine mists
- High CE is achieved with ideal expansion of the fine mists to match the CO₂ laser beam diameter

Long Life Chamber

- Debris mitigation by superconducting magnets
- Ionized tin atoms are guided to tin catchers by the magnetic field



SM3 is the basis of debris mitigation system.



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"SM3": Superconducting Magnet Mitigation Method



- Minimum amount of Sn
 - 20um diameter droplet
- 100% ionization in plasma emission
 - Pre pulse technology
 - Precise shooting control
 - Solid beam profile of laser
- Sn ion trap by magnetic field
 - Not to reach the collector surface
- Sn etching even after deposition
 - $Sn + 2H_2 + EUV \rightarrow SnH_4$



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Debris Mitigation and Capping Layer Evaluations with a Dummy Mirror



Purpose

• Evaluation of tin deposition distribution on the collector mirror

Method

- Dummy collector mirror (no coating)
- Sampling plate (sample coupon) size: 15mmx15mmx0.7mmt material : Si plate (46 pieces)

+multi layer (Si/Mo) + Capping layer

Analysis after test

- Surface condition : SEM
- Deposited tin thickness : XRF
- Capping layer thickness: TEM



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Difference of Deposition on the Sample Coupons of a Dummy Mirror

Capping layer disappearance Blister generation Capping layer deformation Blister generation Capping layer survived No blister generation



The capping layer material has great influence on ML durability.



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Debris Mitigation Concept; Tin Stopping



Tin stopping

- Tin is ionized effectively by double pulse irradiation and precise shooting control
- 2. Tin ions are confined by magnetic field and stopped by H_2 gas to prevent the sputtering to the coating of mirror.
- 3. Confined tin ions are guided and exhausted by H₂ flow from vessel.



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Debris Mitigation Concept; Tin Cleaning

Tin cleaning

- 1. Tin, not confined by magnetic field, are stopped by H_2 gas in order to prevent the sputtering to the coating of collector.
- 2. Deposited tin on the collector is etched by H radical gas.

3. Cooling and gas flow systems for preventing decomposition of SnH₄



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Slide 29

Collector lifetime status after improvement

Power level of EUV: 100W in Burst, (= 2mJ x 50kHz), 33% duty cycle, 30W in average.
 Collector lifetime was improved to -0.4%/Bpls by magnetic debris mitigation technology optimization.



SUMMARY



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Summary

Pilot#1 for HVM is now under construction, and shows promising results;

- Demonstrated 113W in-burst power at 75% duty (85W average) for 143 hours based on the preliminary results of CE 5%, 250W power with Proto#2
- Next target : 250W full specification operation with long term by 1H 2018.

Pilot#1 Collector Mirror test shows HVM capable lifetime;

 Superconducting Magnet Mitigation Method "SM3" realized the reflectance degradation rate of 0.4%/Bpls at over 100W level operation (in burst mode, up to 30Bp).

Pilot#1 shows HVM ready availability;

Pilot#1 system achieved the potential availability of 89% (2week-average).

Will Gigaphoton's Source be in time to meet145wph HVM by 2019 ? Yes, Gigaphoton's Source will be in time to meet145wph HVM by 2019 .



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THANK YOU

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